

Microwave Probe Test Evaluation on Teradyne A585

Motivation

Challenge

Calibration Concept

Test H/W of TRF1012

Probe Interface

Measurement Results

Conclusion





Joerg Paulus Texas Instruments



Michael Janssen Texas Instruments



Harald Parzhuber Texas Instruments



Dieter Luecking Teradyne



Manfred Kanther Texas Instruments



Detlef Bergmann Teradyne



# Motivation

Discover wafer process influences to the RF performance at wafer level already.

Perform a device RF performance validation as soon as silicon is available.

Potential for Die delivery to customers demands for a full performance probe test.

Advanced packaging methods like flip-chip will require RF probing.

Interleave testing between probe and final test improves the test efficiency and reduces cost.



## Challenge

Establish controlled impedance transmission lines to the device bond pads.

Establish an RF probe test setup calibration process at wafer level.

# Solution Strategy

Utilize overhead testhead docking system of A580 tester.

Utilize probe card POGO/OSP connection system for flexible probe card changes.

Utilize Cascade's Membrane probe contact technology.

Generate wafer standards for test system calibration.



## **Calibration Concept**

High Frequency parametric tests demand for a calibrated test setup.

The reference level or calibration point of supplied and measured signals should be the die pad for bare dies.

Calibration structures like 50 ohm resistors, Opens and Shorts are needed.





## **DECT RF Transceiver**



- VCC = 3.0V +/- 10%
- Receiver Sensistivity = -90dBm. -> 8dB NF at Antenna. -> 5.5dB NF at Image Reject Mixer
- Receiver Intermodulation Rejection. IP3 = -23dBm at Antenna -> -25dBm at Receiver input
- RF VCO Phase Noise = -106dBc/Hz @ 1MHz offset
- Receiver RSSI. Dynamic range = 70dB. Linear over: RFin = -93dBm (antenna) -> VRssi = 0.75V

RFin = -33dBm (antenna) -> VRssi = 1.96V

• Transmit Output Level = 0dBm



Chip Photo TRF1012









#### **Test Schematic**









# Details of the TERADYNE / CASCADE Probe card









# **PIB shown with RF semi-rigid cabling**











#### **Correlation Data**

10.000 9.000 8.000 7.000 6.000 g 5.000 \_\_\_\_NF, A585 NF, Bench 4.000 3.000 2.000 1.000 0.000 1500 1520 1540 1560 1580 1600 1620 1640 1660 1680 1700 1720 1740 1760 1780 1800 1820 1840 1860 1880 1900 1920 1940 1980 2000 MHz

DIE1 S21 & NF (3.0V, 30uA)



## **Conclusion**

A probe test setup was established with controlled impedance lines from the tester microwave source to the device bond pad.

Special calibration wafers with calibration structures were manufactured for complete probe card de-embedding.

Special LNA wafer was designed and processed for probe test to lab measurement correlation study.

Acceptable repeatability and reproducibility of RF measurements at wafer probe were achieved.

A correlation study of RF measurements at wafer probe and in the lab revealed that the different test environment must be taken into account to assess the results correctly.